Supplementary Information

Green-solvent-processed formamidinium-based perovskite solar cells with uniform grain growth and strengthened interfacial contact via nanostructured tin oxide layer

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Fig. S1 XRD patterns from top-surfaces of perovskite films prepared via green solvent and toxic solvent, respectively.



Fig. S2 (a) Top-view SEM image and **(c)** the size distribution of perovskite film based on SnO₂-NRs, respectively. **(b)** Top-view SEM image and **(d)** the size distribution of perovskite film based on SnO₂-NP, respectively.



Fig. S3 The deionized water contact angles of (a) the SnO_2 -NRs and (b) SnO_2 -NP prepared on FTO substrates.



Fig. S4 Integrated intensity profiles along the q_z direction of GIWAXS pattern for SnO₂-NRs and SnO₂-NP substrates.



Fig. S5 UV-vis transmittance of bare FTO glass, SnO_2 -NP, and SnO_2 -NRs in different reaction temperature. The inset shows a typical optical image of the bare FTO glass and FTO/NRs-ii.



Fig. S6 Diffuse reflectance spectra of different films.



Fig. S7 (a) Schematic of the fabrication procedures of SnO₂-NRs. Top-view and cross-sectional SEM images of SnO₂-NRs in different reaction temperature: **(b)** NRs-i sample at 180°C, **(c)** NRs-ii sample at 200°C, and **(d)** NRs-iii sample at 220°C, respectively.



Fig. S8 TEM and HR-TEM images of SnO₂-NRs scraped from NR-ii sample.



Fig. S9 High-angle annular dark-field (HADDF) STEM image of NRs-ii and energy dispersive X-ray (EDX) elemental mapping images of O, Sn elements.



Fig. S10 Top-view and cross-sectional SEM images of perovskite film based on (a) NRs-i ETL substrate at 180°C, (b) NRs-iii ETL substrate at 220°C



Fig. S11 Current-voltage curves of PSCs based on commercial SnO₂-NP and SnO₂-NRs in different reaction temperature: NRs-i sample at 180°C, NRs-ii sample at 200°C, and NRs-iii sample at 220°C, respectively.



Fig. S12 Charge transfer density difference plots for **(a)** $H(CH_2)_4Cl$ ("Cl-BSM") and **(b)** $H(CH_2)_4H$ ("H-BSM") interfaced with I-terminated MAPbI₃ (001) surface. Dashed lines across the interface indicate no bonding.



Fig. S13 XPS spectra from top-surface of SnO₂-NRs (control) and Cl-BSM/SnO₂-NRs (w/Cl-BSM): (a) typical XPS survey, (b) Si 2p core level and (c) Cl 2p core level.



Fig. S14 The deionized water contact angles of SnO₂-NRs/Cl-BSM prepared on FTO substrates.



Fig. S15 (a) Top-view SEM image of the perovskite film based on Cl-BSM/SnO₂-NRs and **(b)** cross-sectional SEM image of PSCs device.



Fig. S16 The size distribution of perovskite film based on SnO_2 -NRs/Cl-BSM substrate.



Fig. S17 (a) 2D GIWAXS patterns of perovskite film deposited on SnO_2 -NRs/Cl-BSM coated quartz substrates, (b) Integrated intensity profiles along the q_z direction of GIWAXS pattern for SnO_2 -NRs and SnO_2 -NRs/Cl-BSM substrates.



Fig. S18 (a) HAADF-STEM cross-sectional image (top) and zoom-in image of selected area (bottom) of Cl-BSM/SnO₂-NRs grown on FTO substrate. **(b)** EDX cross-sectional elemental mapping images of Sn, Si and Cl elements for Cl-BSM/SnO₂-NRs.



Fig. S19 (a) EDX elemental mapping and **(b)** EDX spectrum of PVK films based on Cl-BSM/SnO₂-NRs.



Fig. S20 (a) The X-Z Slice and (b) 3D render of various elements SIMS data.



Fig. S21 Transmittance spectra based on bare FTO, SnO₂-NRs, and the Cl-BSM/SnO₂-NRs substrates, respectively.



Fig. S22 Equivalent circuit of PSCs based on SnO₂-NRs and SnO₂-NRs/Cl-BSM used for fitting impedance data.



Fig. S23 The UPS spectra on perovskite, SnO_2 -NRs and Cl-BSM/SnO₂-NRs films: (a) Valance regions (E_{onset}) and (b) secondary-electron cutoff (E_{cutoff}). The values of E_{onset} are 1.45 eV, 4.05 eV and 4.03 eV for perovskite, SnO_2 -NRs and Cl-BSM/SnO₂-NRs, respectively. The conduction band minimum (E_{CB}) can be calculated from the formular $E_{CB} = WF + E_{onset} - E_g$, which are 3.99 eV, 4.16 eV and 4.03 eV for perovskite, SnO_2 -NRs and Cl-BSM/SnO₂-NRs, respectively.



Fig. S24 Tauc plot of (a) perovskite and (b) SnO_2 -NRs and SnO_2 -NRs/Cl-BSM films.



Fig. S25 KPFM images of (a) SnO₂-NRs and (b) SnO₂-NRs/Cl-BSM films.



Fig. S26 Current-voltage curves of PSCs based on commercial SnO₂-NP and SnO₂-NRs/Cl-BSM, respectively. Inset shows the relevant paraments of PSCs.



Fig. S27 Top-view SEM images of perovskite film based on SnO_2 -NPs and SnO_2 -NRs/Cl-BSM, respectively.



Fig. S28 The size distribution of perovskite film based on SnO₂-NPs and SnO₂-NRs/Cl-BSM, respectively.

host-solvent	anti-solvent/ air knife	PSCs structure	PCE/ %	year
non-green	Green			
DMF/DMSO	diisopropyl	FTO/cTiO ₂ /mTiO ₂ /Li-	21.26	20221
	ether	TiO ₂ /perovskite/Spiro/Au		
DMF/DMSO	ethyl acetate /hexane	ITO/SnO ₂ /perovskite/Spiro/Ag	20.06	2019 ²
DMF/DMSO	anisole	FTO/cTiO ₂ /mTiO ₂ /Li-TiO ₂ / perovskite/Spiro/Au	20.2	2018 ³
DMF/DMSO	methyl benzoate	FTO/SnO ₂ /perovskite/Spiro/Au	22.37	20204
DMF/DMSO	tetraethyl orthosilicate	ITO/NiO _x /perovskite/PCBM/BCP/Ag	18.15	20205
DMF/DMSO	methylamine bromide/ethane	ITO/PTAA/perovskite/PC ₆₁ BM/Phen- NADPO/Ag	21.53	20206
DMF/DMPU	air knife	FTO/SnO ₂ /perovskite/Spiro/Au	20.56	20217
DMF/NMP	antisolvent-free	FTO/SnO ₂ /perovskite/Spiro/Au	24.02	20228
Green	Green			
DMSO	isopropanol	ITO/NiO _x /PTAA/perovskite/PC ₆₁ BM/ BCP/Ag	19.5	20219
DMSO	antisolvent-free	ITO/PTAA /SiO ₂ -	16.7	202110
		NP/perovskite/PCBM/BCP/Ag		
DMSO/GBL	antisolvent-free	FTO/NiO _x /perovskite/PCBM/PEI/BC P/Ag	17.02	202011
2-Me/ACN	air knife	ITO/PTAA/perovskite/C ₆₀ /BCP/metal cathode	21.3	201912
2-Me/NMP	antisolvent-free	ITO/MeO- 2PACz/perovskite/PC ₆₀ BM/ BCP/Ag	20.39	2022 ¹³
2-Me/DMSO /MA ethanol	antisolvent-free	FTO/SnO ₂ /perovskite/Spiro/Au	18.27	202214
TMP/DMF	dibutyl ether	FTO/SnO ₂ /perovskite/Spiro/Au	20.02	202115
TEP	dibutyl ether	FTO/SnO ₂ /KCl/perovskite/PEAI/Spir o/Au	20.1	2022 ¹⁶
TEP	dibutyl ether	FTO/SnO ₂ -NRs/Cl-	22.42	This
	-	BSM/perovskite/Spiro/Ag		work
2-Me	antisolvent-free	FTO/SnO ₂ -NRs/Cl-	20.77	This
		BSM/perovskite/Spiro/Ag		work

Table S1 Performance comparison of recent works about green-solvent engineering

Table S2. Photovoltaic parameters of the PSCs based on commercial SnO₂-NP and SnO₂-NRs in different reaction temperature: NRs-i sample at 180°C, NRs-ii sample at 200°C, and NRs-iii sample at 220°C, respectively.

ETL substrates	J _{sc} (mA/cm ²)	V _{oc} (V)	FF (%)	PCE (%)
SnO ₂ -NP	23.66	1.00	81.04	19.17
NRs-i	24.01	0.96	67.82	15.63
NRs-ii	24.30	1.02	77.86	19.30
NRs-iii	23.87	1.02	74.31	18.09

Table S3. DFT results for E_{int} for "BSM" on different surface terminations of MAPbI₃ (010). Here, "——" indicates bond formation with charge transfer, and "---" indicates no chemical bond formation

"BSM"/Termination per cell	Cl-	H-	Cl-	H-	
	SMB/MAI-	SMB/MAI-	SMB/PbI2-	SMB/PbI ₂ -	
E_{int}/eV	-0.176944	-0.147035	-0.465694	-0.226885	
Bond Type (Length, Å)	Cl—I	HI	Cl—Pb	H Pb	
	(3.42567)	(3.44440)	(3.19359)	(3.18806)	

Table S4. PL decay lifetimes of PVK films on SnO2-NRs (control) and SnO2-NRs/Cl-BSM (w/Cl-BSM) coated FTO substrates.

Substrate	$\tau_1(ns)$	A ₁	$\tau_2(ns)$	A ₂	$\tau_t(ns)$
Control	1.063	6588.92	78.103	543.47	67.19
w/Cl-BSM	1.797	1171.92	39.714	694.61	37.02

Table S5. The detailed photovoltaic parameters of the champion devices with or without Cl-BSM measured in reverse scan and forward scan at a scan rate of 100 mV/s under simulated AM 1.5G one sun illumination of 100mW/cm^2

	Scan	J _{sc}	J _{sc} from				h (%)
Device	direction	(mA/cm ²)	EQE	$V_{oc}(V)$	FF (%)	PCE (%)	
control	reverse scan	24.3	23.3	1.02	77.86	19.3	23.4
	forward scan	24.17		0.92	70.31	15.64	
	reverse scan	24.6		1.12	81.36	22.42	2.6
w/Cl-BSM	forward scan	24.3	24.2	1.12	80.24	21.84	

References

- L. Wang, X. Wang, L.-L. Deng, S. Leng, X. Guo, C.-H. Tan, W. C. H. Choy, C.-C. Chen, *Materials Horizons*, 2020, 7, 934-42.
- [2] H. B. Lee, M. K. Jeon, N. Kumar, B. Tyagi, J. W. Kang, Advanced Functional Materials, 2019, 29, 1903213.
- [3] M. Yavari, M. Mazloum-Ardakani, S. Gholipour, M. M. Tavakoli, S.-H. Turren-Cruz, N. Taghavinia, M. Grätzel, A. Hagfeldt, M. Saliba, *Advanced Energy Materials*, 2018, 8, 1800177.
- Y. Yun, F. Wang, H. Huang, Y. Fang, S. Liu, W. Huang, Z. Cheng, Y. Liu, Y. Cao, M. Gao, L. Zhu, L. Wang, T. Qin, W. Huang, *Adv Mater*, 2020, 32, e1907123.
- [5] M. Wang, Q. Fu, L. Yan, J. Huang, Q. Ma, M. Humayun, W. Pi, X. Chen, Z. Zheng, W. Luo, *Chemical Engineering Journal*, 2020, **387**, 123966.
- [6] W. Xu, Y. Gao, W. Ming, F. He, J. Li, X. H. Zhu, F. Kang, J. Li, G. Wei, Adv Mater, 2020, 32, e2003965.
- [7] D. Lee, K. Lim, J. Lee, N. Park, *Journal of Materials Chemistry A*, 2021, 9, 3018-3028.
- [8] T. Bu, L. Ono, J. Li, J. Su, G. Tong, W. Zhang, Y. Liu, J. Zhang, J. Chang, S. Kazaoui, F. Huang, Y.-B. Cheng, Y. Qi, *Nature Energy*, 2022, 7, 528-536.
- [9] S. Shan, Y. Li, H. Wu, T. Chen, B. Niu, Y. Zhang, D. Wang, C. Kan, X. Yu, L. Zuo, H. Chen, *SusMat*, 2021, 1, 537-44.
- [10] J. Küffner, J. Hanisch, T. Wahl, J. Zillner, E. Ahlswede, M. Powalla, ACS Applied Energy Materials, 2021, 4, 11700-10.
- [11] H. Huang, Y. Tian, C. Huang, F. Li, C. Chu, M. Lee, C. Huang, F. Su, ACS Appl Mater Interfaces, 2020, 12, 26041-9.
- [12] Y. Deng, C. Van Brackle, X. Dai, J. Zhao, B. Chen, J. Huang, *Sci Adv*, 2019, 5, eaax7537.
- [13] S. Lee, S. Hong, H. Kim, ACS Appl Mater Interfaces, 2022, 14, 39132-39140.
- [14] Q. Zhang, G. Ma, A. Green, K. Gollinger, J. Moore, T. Demeritte, C. Ray, A.

Hill, X. Gu, E. Morgan, M. Feng, S. Banerjee, Q. Dai, ACS Applied Energy Materials, 2022, 5, 1487-1495.

- [15] Yun. Y, Vidyasagar. D, Lee. M, Gong. O. Y, Jung. J, Jung. H. S, Kim. D. H, Lee. S, Adv Sci, 2021, 8, e2102492-501.
- [16] Cao. X, Hao. L, Liu. Z, Su. G, He. X, Zeng. Q, Wei. J, *Chemical Engineering Journal*, 2022, **437**, 135458-66.